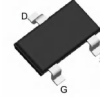


Description

The TX3422MI uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



SOT23-3L

General Features

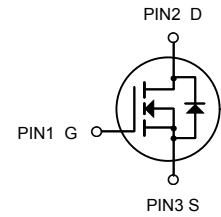
$V_{DS} = 60V, I_D = 4.5A$

$R_{DS(ON)} < 75m\Omega @ V_{GS}=10V$

$R_{DS(ON)} < 90m\Omega @ V_{GS}=4.5V$

Application

High power and current handing capability
Lead free product is acquired
Surface mount package
PWM applications
Load switch
Power management



N-Channel MOSFET

Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous	4.5	A
I_{DM}	Drain Current-Pulsed (Note 1)	15	A
P_D	Maximum Power Dissipation	8	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}C$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2)	89	$^{\circ}C/W$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=5A$	---	70	75	m Ω
		$V_{GS}=4.5V, I_D=5A$	---	80	90	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	---	2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=48V, V_{GS}=0V, T_J=25^{\circ}\text{C}$	---	---	1	μA
		$V_{DS}=48V, V_{GS}=0V, T_J=55^{\circ}\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=5A$	---	7	---	S
Q_g	Total Gate Charge (10V)	$V_{DS}=12V, V_{GS}=10V, I_D=5A$	---	5.5	---	nC
Q_{gs}	Gate-Source Charge		---	1.8	---	
Q_{gd}	Gate-Drain Charge		---	2.4	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=12V, V_{GS}=10V, R_G=3.3\Omega, I_D=5A$	---	6	---	ns
T_r	Rise Time		---	10	---	
$T_{d(off)}$	Turn-Off Delay Time		---	15	---	
T_f	Fall Time		---	7	---	
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	695	---	pF
C_{oss}	Output Capacitance		---	148	---	
C_{rss}	Reverse Transfer Capacitance		---	7	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	17	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	50	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^{\circ}\text{C}$	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=15A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

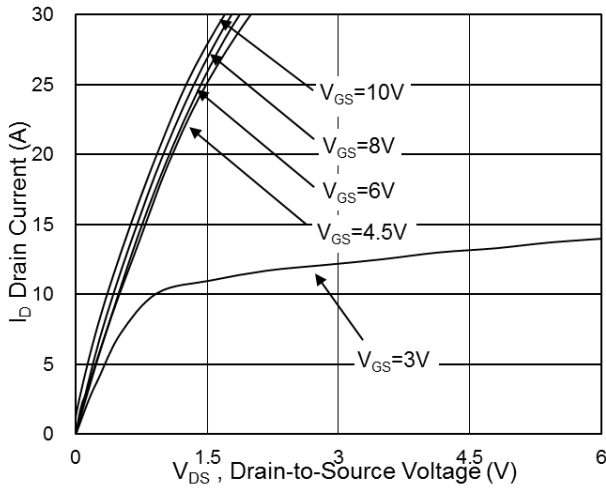


Fig.1 Typical Output Characteristics

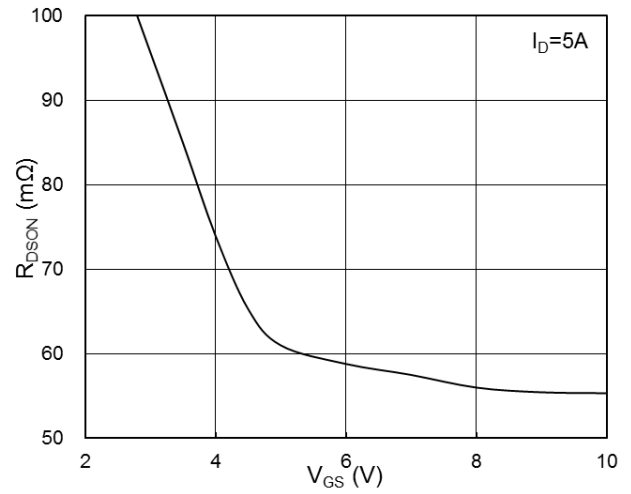


Fig.2 On-Resistance vs. Gate-Source Voltage

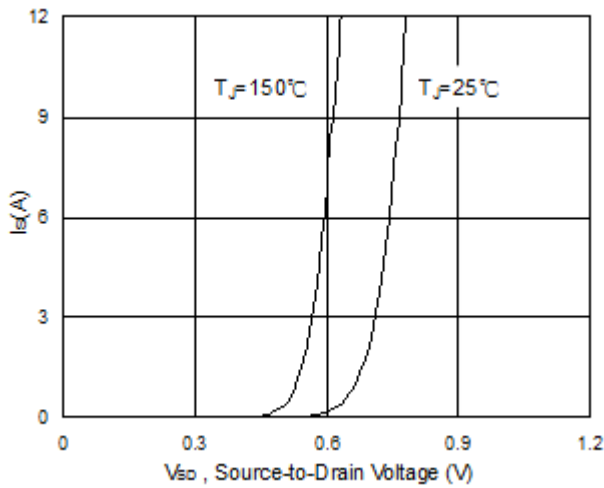


Fig.3 Forward Characteristics of Reverse

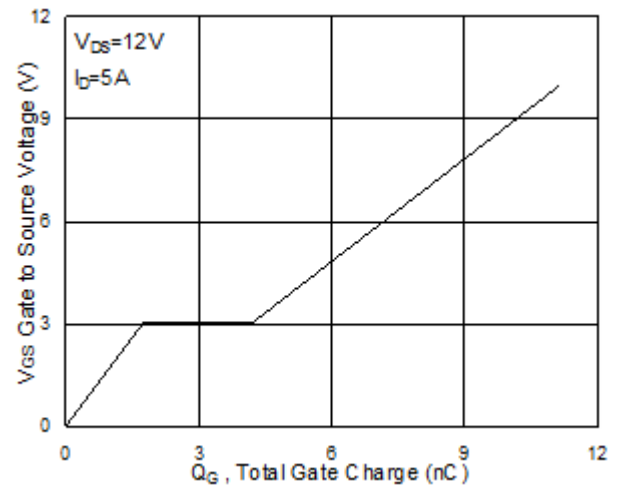


Fig.4 Gate-Charge Characteristics

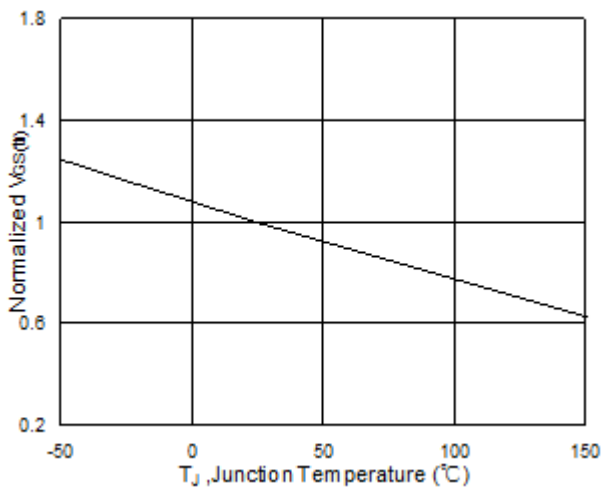


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

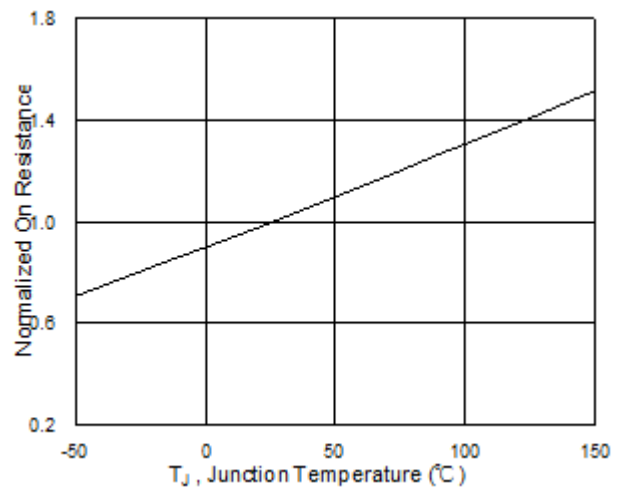


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

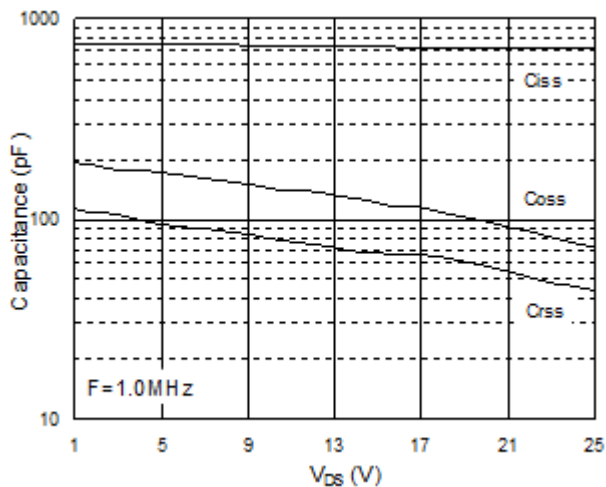


Fig.7 Capacitance

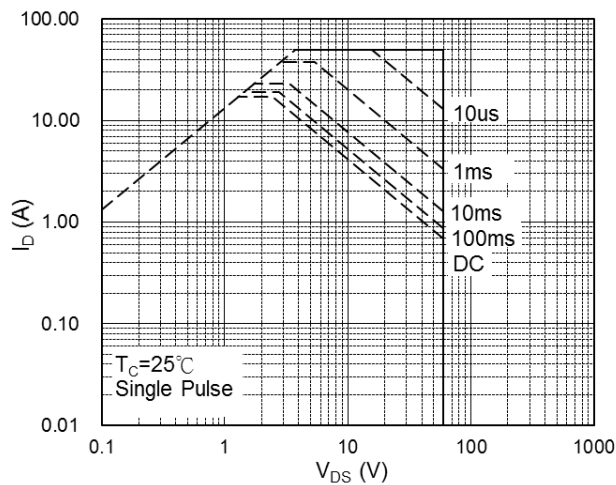


Fig.8 Safe Operating Area

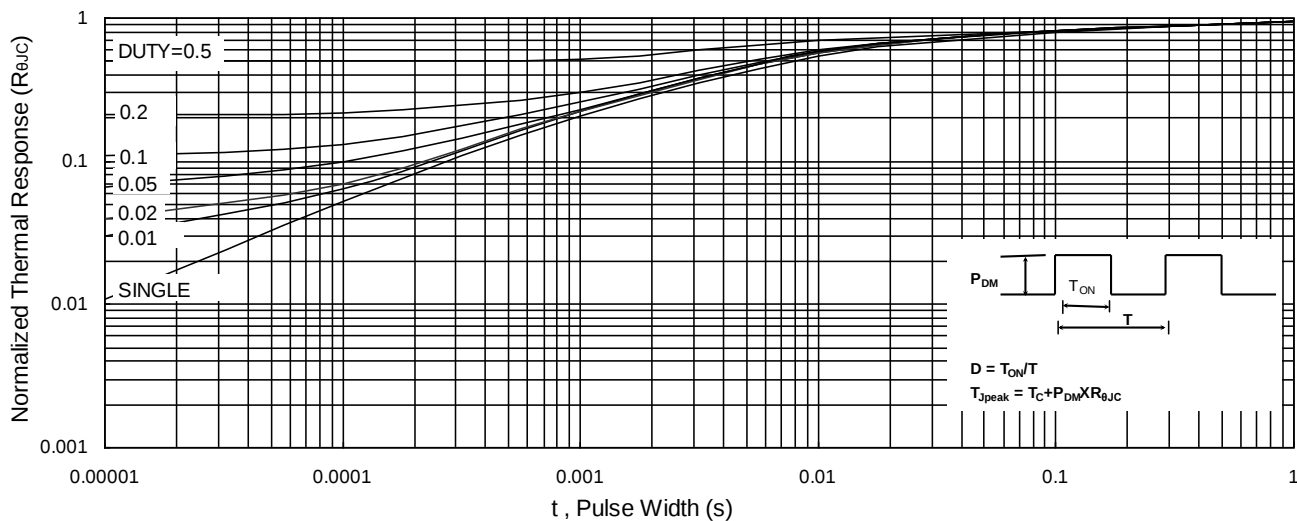


Fig.9 Normalized Maximum Transient Thermal Impedance

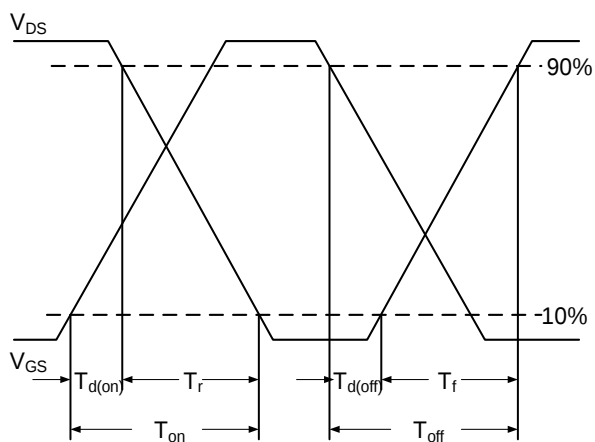


Fig.10 Switching Time Waveform

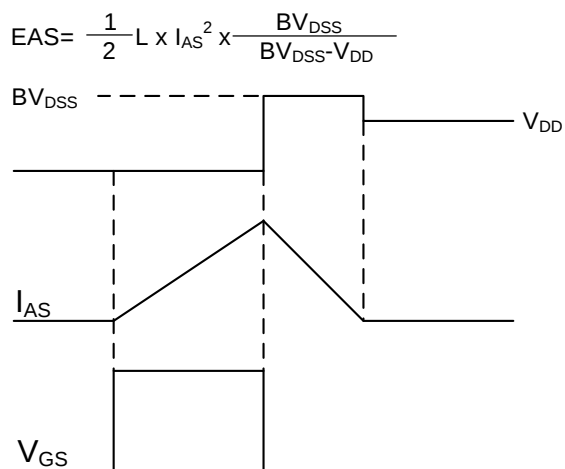
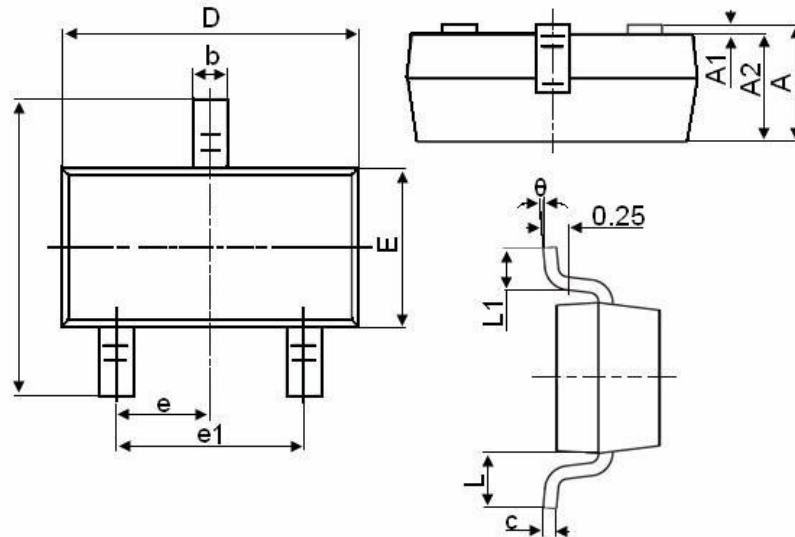


Fig.11 Unclamped Inductive Switching Waveform

SOT23-3L Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.800	3.000
E	1.500	1.700
E1	2.650	2.950
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.600
θ	0°	8°

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